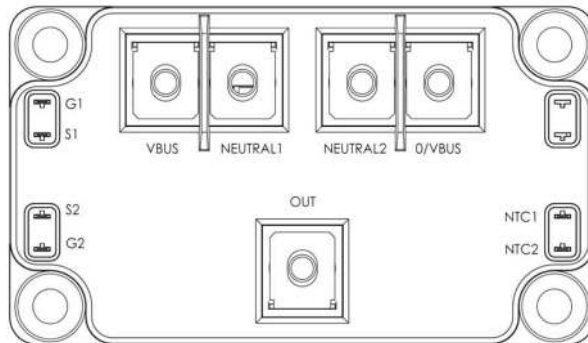
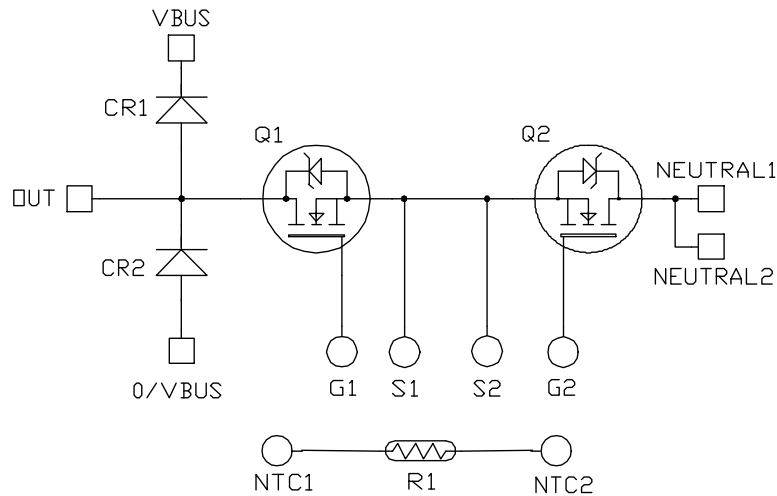


Vienna Rectifier SiC MOSFET Power Module

Product Overview

The MSCSM70VR1M07CT6AG device is a Vienna rectifier 700V, 349A silicon carbide (SiC) power module.



Note: All ratings at $T_J = 25\text{ }^\circ\text{C}$, unless otherwise specified.



These devices are sensitive to electrostatic discharge. Proper handling procedures must be followed.

Features

The following are key features of the MSCSM70VR1M07CT6AG device:

- SiC Power MOSFET
 - Low $R_{DS(on)}$
 - High temperature performance
- SiC Schottky Diode
 - Zero reverse recovery
 - Zero forward recovery
 - Temperature independent switching behavior
 - Positive temperature coefficient on V_F
- Kelvin source for easy drive
- Low stray inductance
- M5 power connectors
- Internal thermistor for temperature monitoring
- Aluminum Nitride (AlN) substrate for improved thermal performance

Benefits

The following are the benefits of MSCSM70VR1M07CT6AG device:

- Outstanding performance at high frequency operation
- High-power and high-efficiency rectifiers and converters
- Direct mounting to heatsink (isolated package)
- Low junction-to-case thermal resistance
- Low profile
- RoHS compliant

Application

The MSCSM70VR1M07CT6AG device is designed for the following applications:

- Power factor correction
- Switched mode power supplies
- Uninterruptible power supplies

1. Electrical Specifications

This section provides the electrical specifications of the MSCSM70VR1M07CT6AG device.

1.1 SiC MOSFET Characteristics (Per SiC MOSFET)

The following table lists the absolute maximum ratings per SiC MOSFET of the MSCSM70VR1M07CT6AG device.

Table 1-1. Absolute Maximum Ratings

| Symbol | Parameter | Maximum Ratings | Unit |
|--------------|----------------------------|----------------------------------|------------|
| V_{DSS} | Drain-Source voltage | 700 | V |
| I_D | Continuous drain current | $T_C = 25\text{ }^\circ\text{C}$ | 349 |
| | | $T_C = 80\text{ }^\circ\text{C}$ | 278 |
| I_{DM} | Pulsed drain current | 700 | |
| V_{GS} | Gate-Source voltage | -10/23 | V |
| $R_{DS(on)}$ | Drain-Source ON resistance | 6.4 | m Ω |
| P_D | Power dissipation | $T_C = 25\text{ }^\circ\text{C}$ | 966 |

The following table lists the electrical characteristics per SiC MOSFET of the MSCSM70VR1M07CT6AG device.

Table 1-2. Electrical Characteristics

| Symbol | Characteristic | Test Conditions | Min. | Typ. | Max. | Unit |
|--------------|---------------------------------|---|-----------------------------------|------|------|---------------|
| I_{DSS} | Zero gate voltage drain current | $V_{GS} = 0V$ $V_{DS} = 700V$ | — | — | 300 | μA |
| $R_{DS(on)}$ | Drain-Source on resistance | $V_{GS} = 20V$ $I_D = 120A$ | $T_J = 25\text{ }^\circ\text{C}$ | — | 5 | 6.4 |
| | | | $T_J = 175\text{ }^\circ\text{C}$ | — | 6.3 | — |
| $V_{GS(th)}$ | Gate threshold voltage | $V_{GS} = V_{DS}$ $I_D = 12\text{ mA}$ | 1.9 | 2.4 | — | V |
| I_{GSS} | Gate-Source leakage current | $V_{GS} = 20V; V_{DS} = 0V$ | — | — | 300 | nA |

MSCSM70VR1M07CT6AG

Electrical Specifications

The following table lists the dynamic characteristics per SiC MOSFET of the MSCSM70VR1M07CT6AG device.

Table 1-3. Dynamic Characteristics

| Symbol | Characteristic | Test Conditions | Min. | Typ. | Max. | Unit | |
|--------------|-------------------------------------|---|-----------------------------------|------|-------|--------------------|----|
| C_{iss} | Input capacitance | $V_{GS} = 0V$ | — | 13.5 | — | nF | |
| C_{oss} | Output capacitance | $V_{DS} = 700V$ | — | 1.5 | — | | |
| C_{rss} | Reverse transfer capacitance | $f = 1\text{ MHz}$ | — | 0.09 | — | | |
| Q_g | Total gate charge | $V_{GS} = -5V/20V$ | — | 645 | — | nC | |
| Q_{gs} | Gate-Source charge | $V_{Bus} = 470V$ | — | 174 | — | | |
| Q_{gd} | Gate-Drain charge | $I_D = 120A$ | — | 105 | — | | |
| $T_{d(on)}$ | Turn-on delay time | $V_{GS} = -5V/20V$ | $T_J = 150\text{ }^\circ\text{C}$ | — | 78 | — | ns |
| T_r | Rise time | $V_{Bus} = 400V$ | | — | 125 | — | |
| $T_{d(off)}$ | Turn-off delay time | $I_D = 240A$ | | — | 214 | — | |
| T_f | Fall time | $R_{G(on)} = 9.4\Omega$ $R_{G(off)} = 5.4\Omega$ | | — | 92 | — | |
| E_{on} | Turn-on energy | $V_{GS} = -5V/20V$ | $T_J = 150\text{ }^\circ\text{C}$ | — | 3 | — | mJ |
| E_{off} | Turn-off energy | $V_{Bus} = 400V$ $I_D = 240A$ $R_{G(on)} = 9.4\Omega$ $R_{G(off)} = 5.4\Omega$ | $T_J = 150\text{ }^\circ\text{C}$ | — | 5.3 | — | |
| R_{Gint} | Internal gate resistance | | — | 1.9 | — | Ω | |
| R_{thJC} | Junction-to-case thermal resistance | | — | — | 0.155 | $^\circ\text{C/W}$ | |

The following table lists the body diode ratings and characteristics per SiC MOSFET of the MSCSM70VR1M07CT6AG device.

Table 1-4. Body Diode Ratings and Characteristics

| Symbol | Characteristic | Test Conditions | Min. | Typ. | Max. | Unit |
|----------|--------------------------|---|------|------|------|---------------|
| V_{SD} | Diode forward voltage | $V_{GS} = 0V; I_{SD} = 120A$ | — | 3.4 | — | V |
| | | $V_{GS} = -5V; I_{SD} = 120A$ | — | 3.8 | — | |
| t_{rr} | Reverse recovery time | $I_{SD} = 120A; V_{GS} = -5V$ | — | 40 | — | ns |
| Q_{rr} | Reverse recovery charge | $V_R = 470V; di_F/dt = 3600\text{ A}/\mu\text{s}$ | — | 1.5 | — | μC |
| I_{rr} | Reverse recovery current | | — | 57 | — | A |

1.2 SiC Diode Ratings and Characteristics (Per SiC Diode)

The following table lists the SiC diode ratings and characteristics of MSCSM70VR1M07CT6AG device.

Table 1-5. SiC Diode Ratings and Characteristics

| Symbol | Characteristic | Test Conditions | Min. | Typ. | Max. | Unit | | |
|------------|-------------------------------------|------------------------------------|-----------------------------------|-----------------------------------|-------|--------------------|---------------|---|
| V_{RRM} | Peak repetitive reverse voltage | | — | — | 1200 | V | | |
| I_{RM} | Reverse leakage current | $V_R = 1200V$ | $T_J = 25\text{ }^\circ\text{C}$ | — | 60 | 800 | μA | |
| | | | $T_J = 175\text{ }^\circ\text{C}$ | — | 100 | — | | |
| I_F | DC forward current | | | $T_C = 100\text{ }^\circ\text{C}$ | — | 200 | — | A |
| V_F | Diode forward voltage | $I_F = 200A$ | $T_J = 25\text{ }^\circ\text{C}$ | — | 1.5 | 1.8 | V | |
| | | | $T_J = 175\text{ }^\circ\text{C}$ | — | 2.1 | — | | |
| Q_C | Total capacitive charge | $V_R = 600V$ | — | 896 | — | nC | | |
| C | Total capacitance | $f = 1\text{ MHz}$ $V_R = 400V$ | — | 984 | — | pF | | |
| | | $f = 1\text{ MHz}$ $V_R = 600V$ | — | 728 | — | | | |
| R_{thJH} | Junction-to-case thermal resistance | | — | — | 0.160 | $^\circ\text{C/W}$ | | |

1.3 Thermal and Package Characteristics

The following table lists the thermal and package characteristics of the MSCSM70VR1M07CT6AG device.

Table 1-6. Thermal and Package Characteristics

| Symbol | Characteristic | Min. | Max. | Unit | | |
|-------------------|--|---------------|-----------------------|------|-----|-----|
| V _{ISOL} | RMS isolation voltage, any terminal to case t = 1 min, 50 Hz/60 Hz | 4000 | — | V | | |
| T _J | Operating junction temperature range | −40 | 175 | °C | | |
| T _{JOP} | Recommended junction temperature under switching conditions | −40 | T _{Jmax} −25 | | | |
| T _{STG} | Storage temperature range | −40 | 125 | | | |
| T _C | Operating case temperature | −40 | 125 | | | |
| Torque | Mounting torque | To heatsink | M6 | 3 | 5 | N.m |
| | | For terminals | M5 | 2 | 3.5 | |
| Wt | Package weight | — | 300 | g | | |

The following table lists the temperature sensor NTC of the MSCSM70VR1M07CT6AG device.

Table 1-7. Temperature Sensor NTC

| Symbol | Characteristic | Min. | Typ. | Max. | Unit |
|-----------------------------------|----------------------------|-------------------------|------|------|------|
| R ₂₅ | Resistance at 25 °C | — | 50 | — | kΩ |
| ΔR ₂₅ /R ₂₅ | — | — | 5 | — | % |
| B _{25/85} | T ₂₅ = 298.15 K | — | 3952 | — | K |
| ΔB/B | — | T _C = 100 °C | 4 | — | % |

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

T: Thermistor temperature
R_T: Thermistor value at T

Note: See [APT0406—Using NTC Temperature Sensor Integrated into Power Module](#) for more information.

1.4 Typical SiC MOSFET Performance Curve

This section shows the typical SiC MOSFET performance curves of the MSCSM70VR1M07CT6AG device.

Figure 1-1. Maximum Thermal Impedance

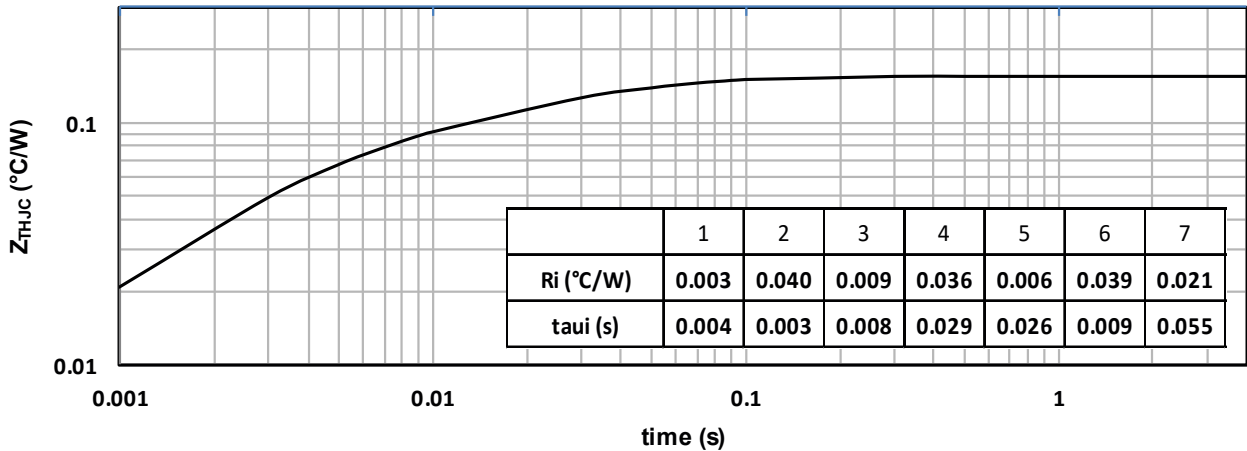


Figure 1-2. Output Characteristics, T_J = 25 °C

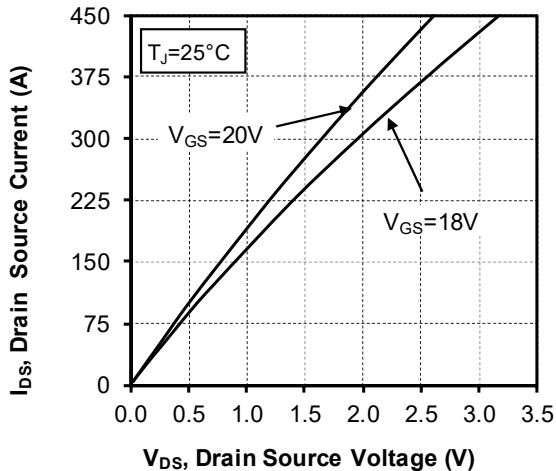


Figure 1-3. Output Characteristics, T_J = 175 °C

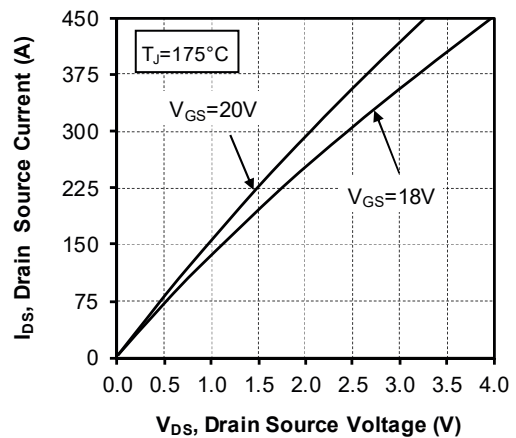


Figure 1-4. Normalized R_{DS(on)} vs. Temperature

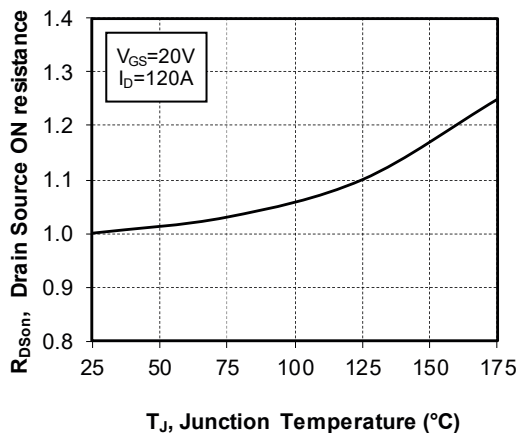
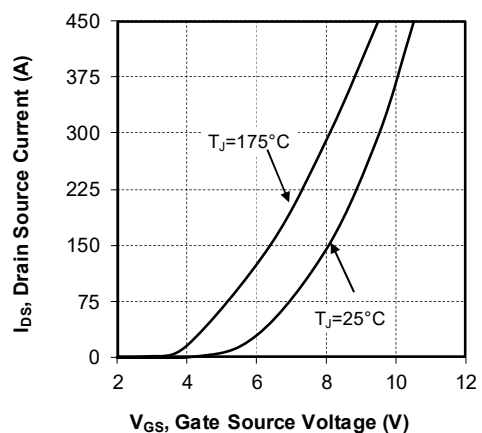


Figure 1-5. Transfer Characteristics



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Figure 1-6. Switching Energy vs. Current

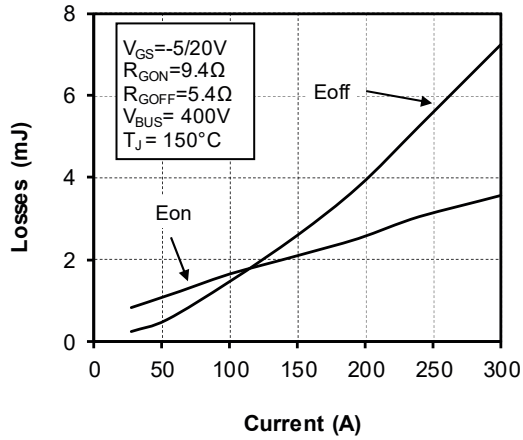


Figure 1-7. Turn On Energy vs. Rg

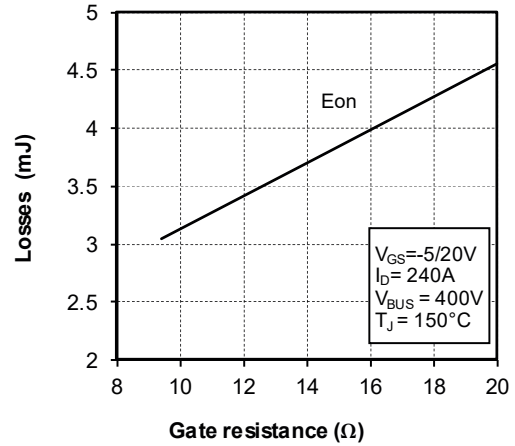


Figure 1-8. Capacitance vs. Drain Source Voltage

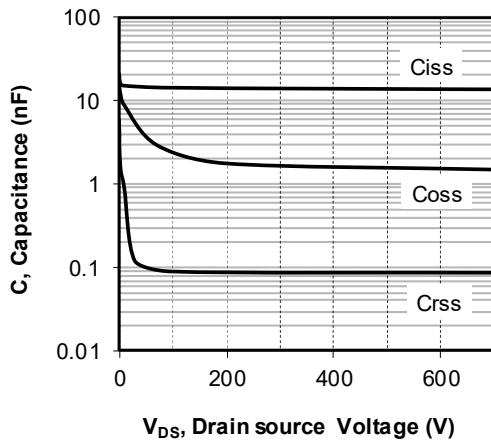


Figure 1-9. Gate Charge vs. Gate Source Voltage

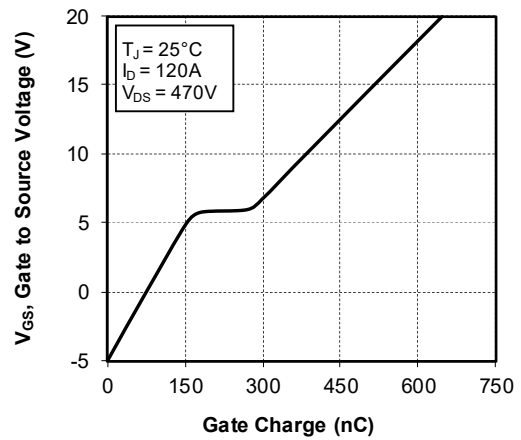


Figure 1-10. Body Diode Characteristics, $T_J = 25^\circ C$

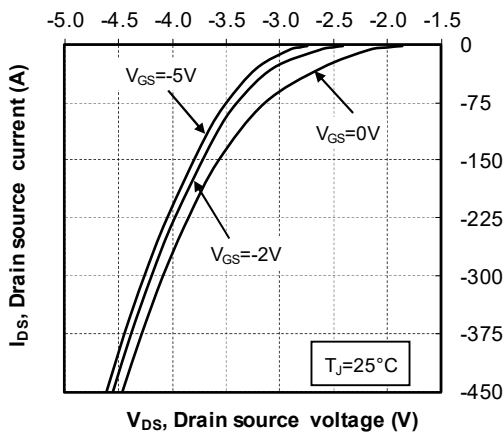
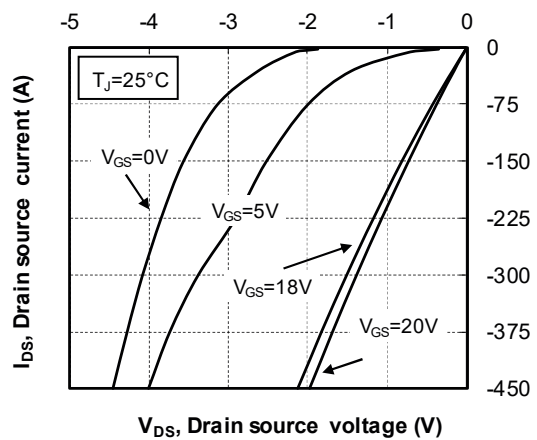


Figure 1-11. 3rd Quadrant Characteristics, $T_J = 25^\circ C$



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Figure 1-12. Body Diode Characteristics, $T_J = 175^\circ\text{C}$

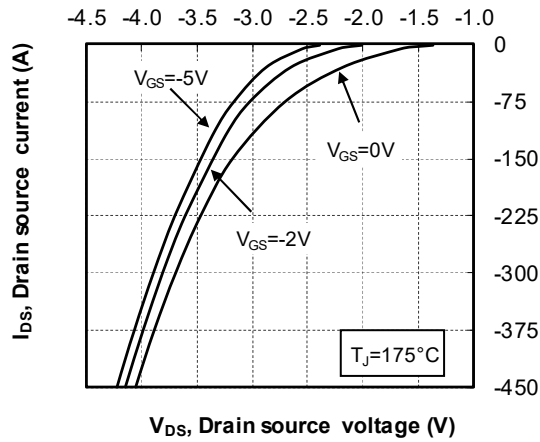


Figure 1-13. 3rd Quadrant Characteristics, $T_J = 175^\circ\text{C}$

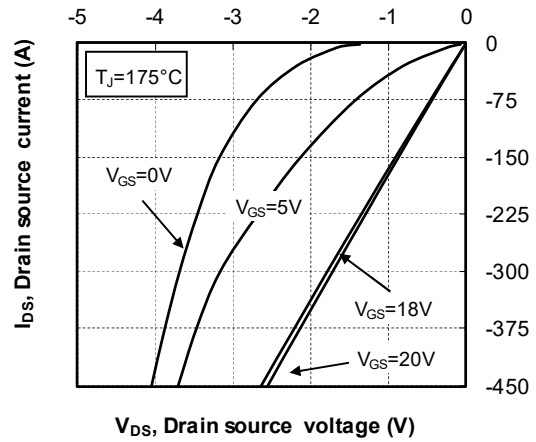


Figure 1-14. Operating Frequency vs Drain Current

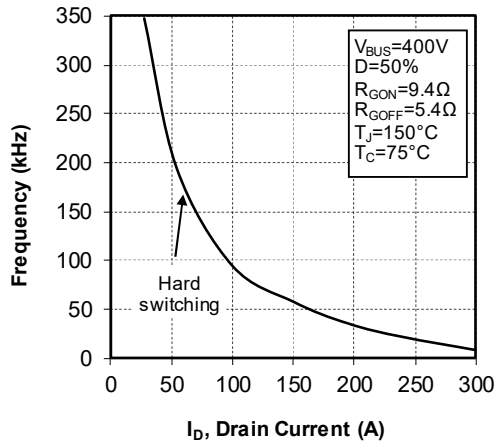
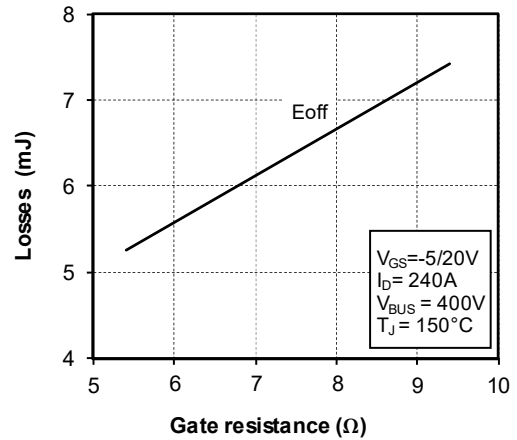


Figure 1-15. Turn Off Energy vs. Rg



1.5 Typical SiC Diode Performance Curves (Per SiC Diode)

This section shows the typical SiC diode performance curves of the MSCSM70VR1M07CT6AG device.

Figure 1-16. Maximum Thermal Impedance

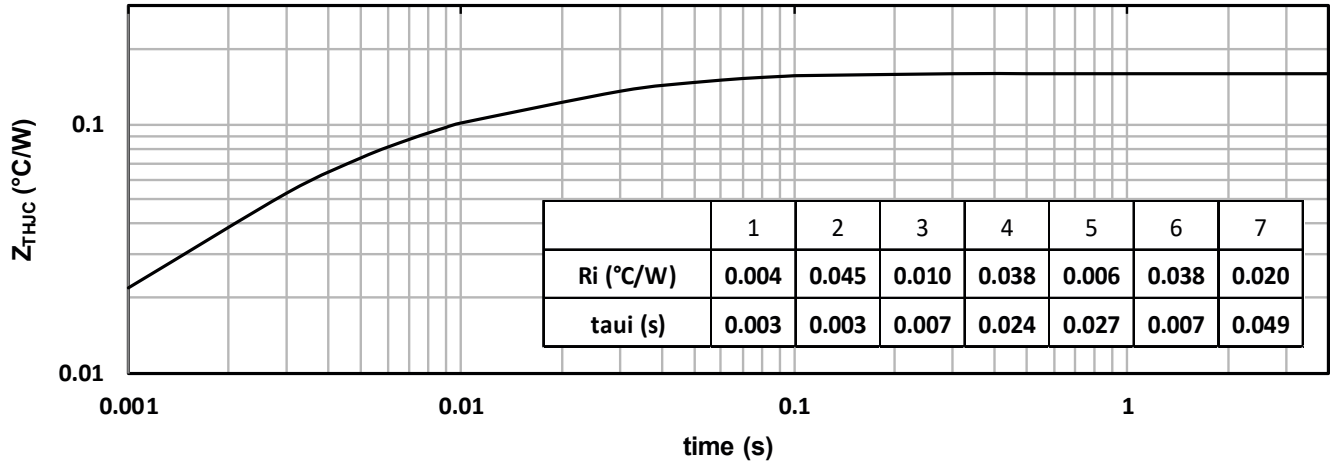


Figure 1-17. Forward Characteristics

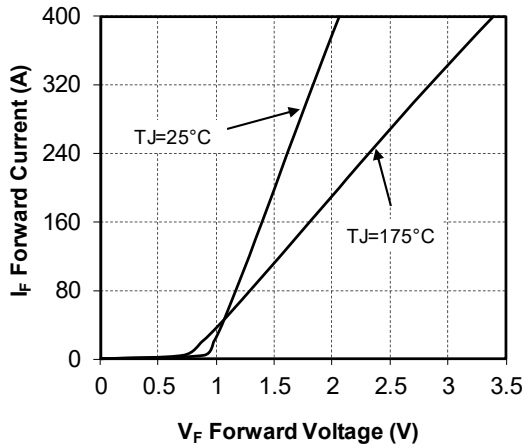
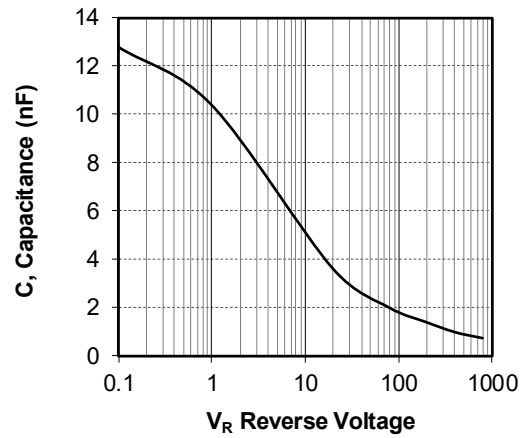


Figure 1-18. Capacitance vs. Reverse Voltage



MSCSM70VR1M07CT6AG

Package Specifications

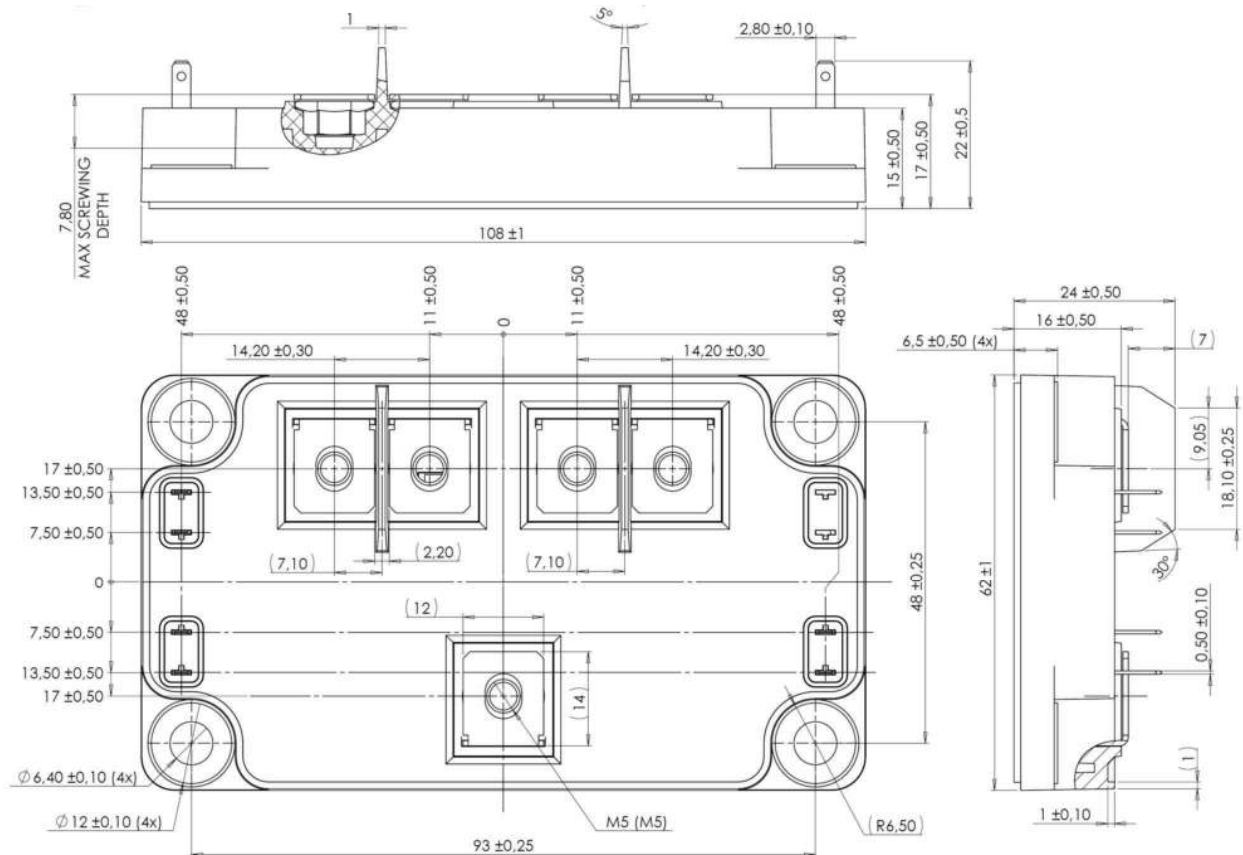
2. Package Specifications

The following section shows the package specification of the MSCSM70VR1M07CT6AG device.

2.1 Package Outline

The following figure shows the package outline drawing of the MSCSM70VR1M07CT6AG device. The dimensions in the following figure are in millimeters.

Figure 2-1. Package Outline Drawing



3. Revision History

| Revision | Date | Description |
|----------|---------|------------------|
| A | 08/2022 | Initial Revision |

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